



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

1.2 Features and benefits

- Low thermal resistance
- Fast switching

1.3 Applications

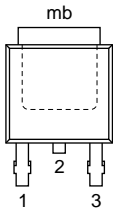
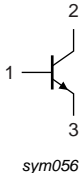
- Electronic lighting ballast
- DC-to-DC converters
- Inverters
- Motor control systems

1.4 Quick reference data

- $V_{CESM} \leq 700 \text{ V}$
- $I_C \leq 8 \text{ A}$
- $P_{tot} \leq 80 \text{ W}$
- $h_{FEsat} = 11 \text{ (typ)}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	base	 <p style="text-align: center;">mb</p> <p style="text-align: center;">1 2 3</p> <p style="text-align: center;">SOT428 (D-PAK)</p>	 <p style="text-align: center;">sym056</p>
2	collector [1]		
3	emitter		
mb	mounting base; connected to collector		

[1] It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.

3. Ordering information

Table 2. Ordering information

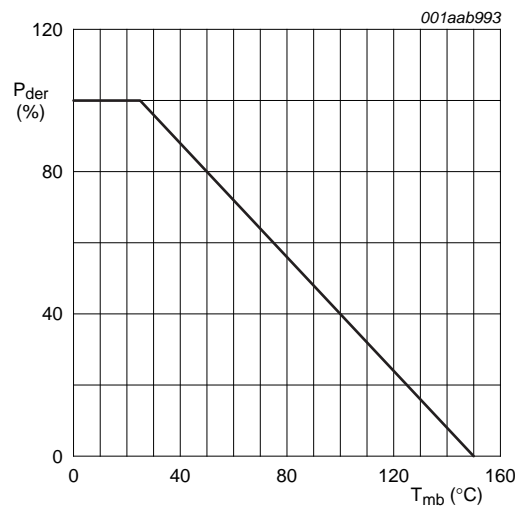
Type number	Package		Version
	Name	Description	
BUJ105AD	D-PAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	peak collector-emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
V_{CBO}	collector-base voltage	open emitter	-	700	V
I_C	collector current (DC)		-	8	A
I_{CM}	peak collector current		-	16	A
I_B	base current (DC)		-	4	A
I_{BM}	peak base current		-	8	A
P_{tot}	total power dissipation	$T_{mb} = \leq 25\text{ °C}$; see Figure 1	-	80	W
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	75	-	K/W

[1] Device mounted on a printed-circuit board; minimum footprint

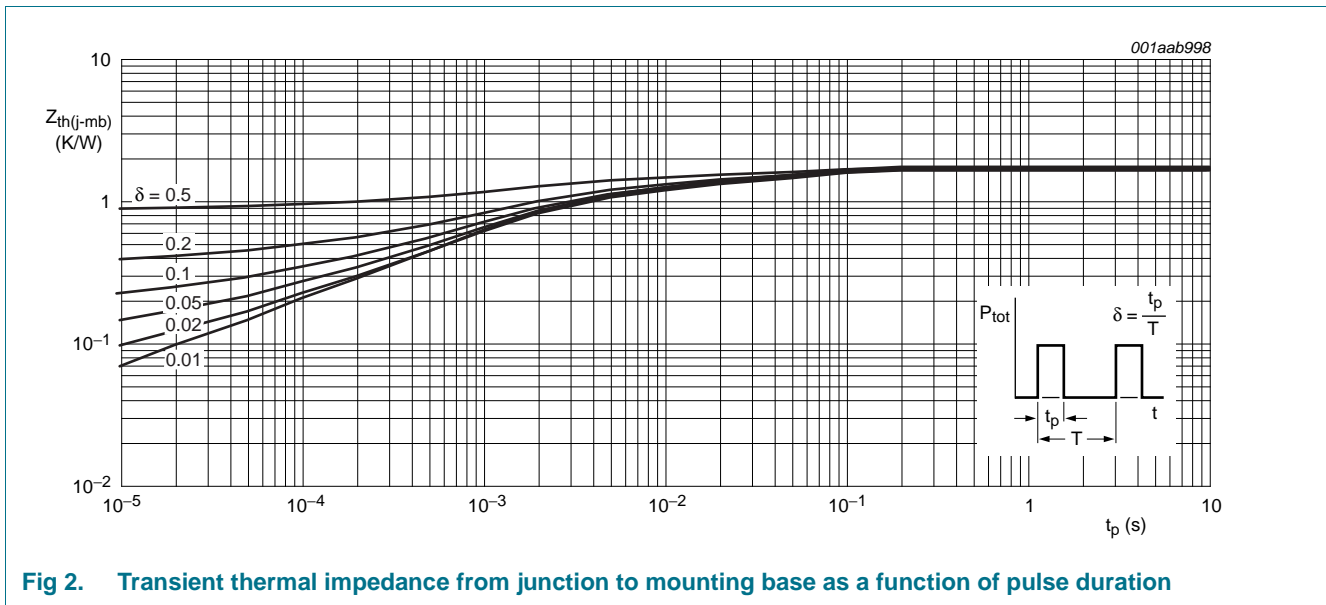


Fig 2. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5. Characteristics

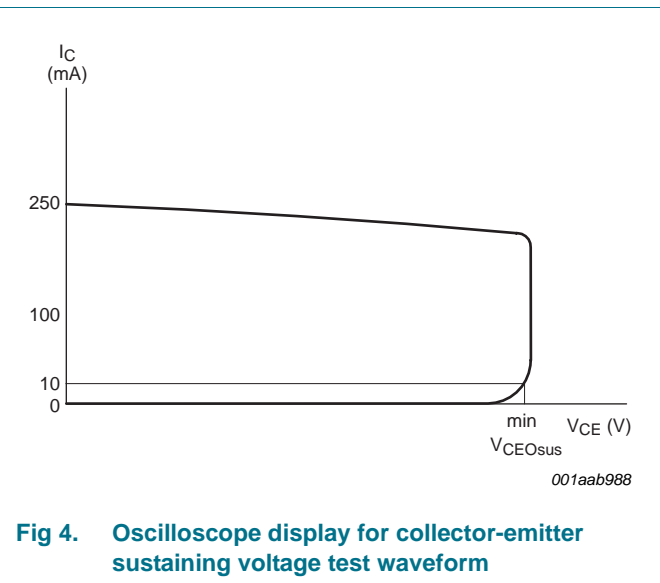
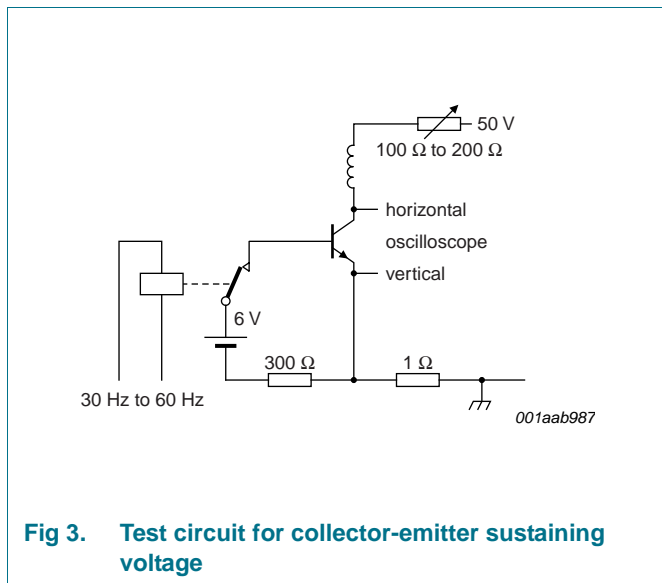
$T_{mb} = 25\text{ }^\circ\text{C}$; unless otherwise specified.

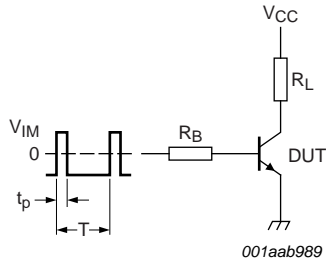
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	[1]	-	0.2	mA
		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}; T_j = 125\text{ }^\circ\text{C}$	[1]	-	0.5	mA
I_{CBO}	collector-base cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	[1]	-	0.2	mA
I_{CEO}	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400\text{ V}$	[1]	-	0.1	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 9\text{ V}; I_C = 0\text{ A}$	-	-	1	mA
V_{CE0sus}	collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA}; L = 25\text{ mH};$ see Figure 3 and 4	400	-	-	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 4.0\text{ A}; I_B = 0.8\text{ A};$ see Figure 11	-	0.3	1.0	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 4.0\text{ A}; I_B = 0.8\text{ A};$ see Figure 12	-	1.0	1.5	V
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	10	14	34	
		$I_C = 500\text{ mA}; V_{CE} = 5\text{ V};$ see Figure 10	13	23	36	
h_{FEsat}	DC saturation current gain	$I_C = 4.0\text{ A}; V_{CE} = 5\text{ V}$	8	11	15	

Table 5. Characteristics ...continued
 $T_{mb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Switching times (resistive load); see Figure 5 and 6						
t_{on}	turn-on time	$I_{Con} = 5\text{ A}$; $I_{Bon} = -I_{Boff} = 1\text{ A}$; $R_L = 75\text{ }\Omega$	-	0.65	1	μs
t_{stg}	storage time		-	1.8	2.5	μs
t_f	fall time		-	0.3	0.5	μs
Switching times (inductive load); see Figure 7 and 8						
t_{stg}	storage time	$I_{Con} = 5\text{ A}$; $I_{Bon} = 1\text{ A}$; $L_B = 1\text{ }\mu\text{H}$;	-	1.2	1.7	μs
t_f	fall time	$V_{BB} = -5\text{ V}$	-	20	50	ns
Switching times (inductive load); see Figure 7 and 8						
t_{stg}	storage time	$I_{Con} = 5\text{ A}$; $I_{Bon} = 1\text{ A}$; $L_B = 1\text{ }\mu\text{H}$;	-	1.4	1.9	μs
t_f	fall time	$V_{BB} = -5\text{ V}$; $T_j = 100\text{ }^{\circ}\text{C}$	-	25	100	ns

[1] Measured with half sine-wave voltage (curve tracer).





$V_{IM} = -6\text{ V to }+8\text{ V}$; $V_{CC} = 250\text{ V}$; $t_p = 20\text{ }\mu\text{s}$;
 $\delta = t_p/T = 0.01$.
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

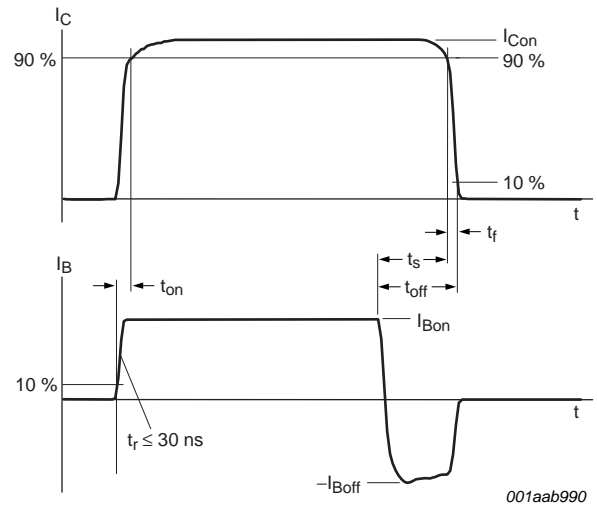
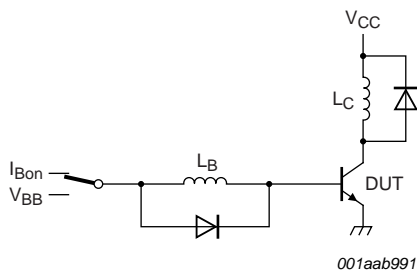


Fig 6. Switching times waveforms for resistive load



$V_{CC} = 300\text{ V}$; $V_{BB} = -5\text{ V}$; $L_C = 200\text{ }\mu\text{H}$; $L_B = 1\text{ }\mu\text{H}$.

Fig 7. Test circuit for inductive load switching

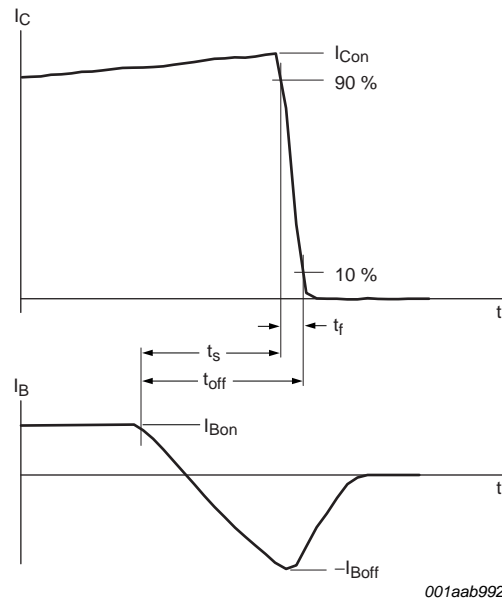


Fig 8. Switching times waveforms for inductive load

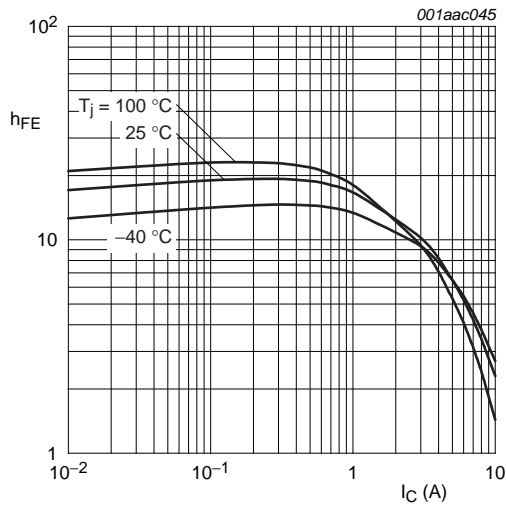


Fig 9. DC current gain as a function of collector current; typical values at $V_{CE} = 1\text{ V}$

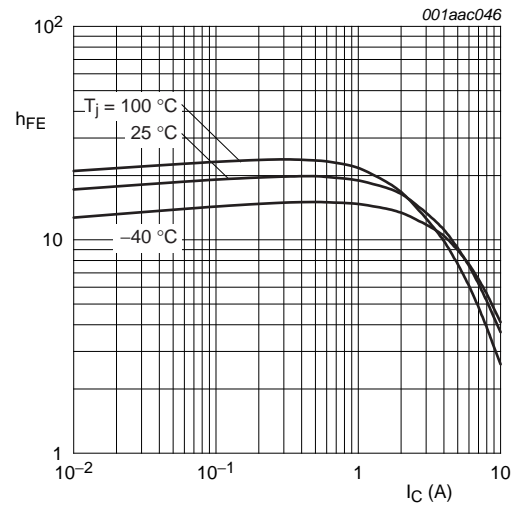
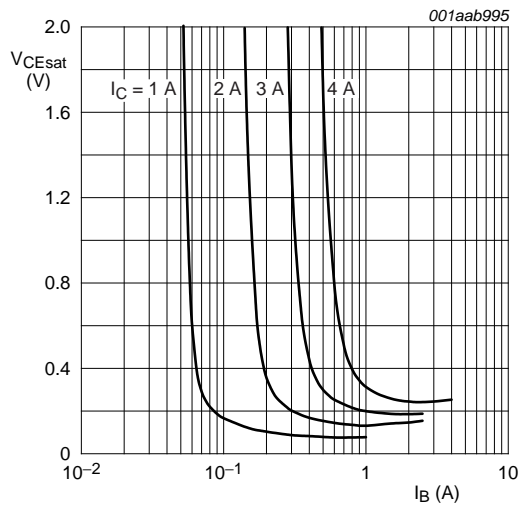
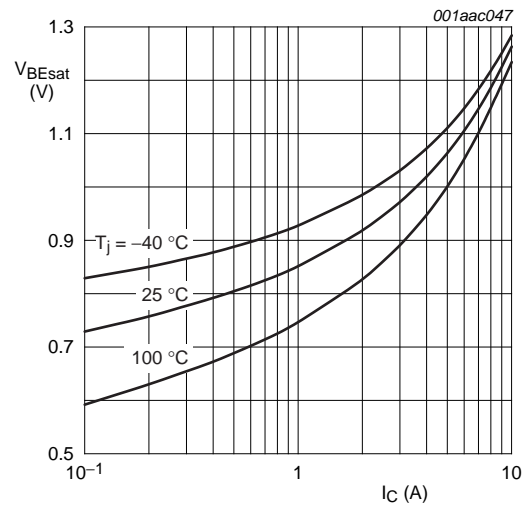


Fig 10. DC current gain as a function of collector current; typical values at $V_{CE} = 5\text{ V}$



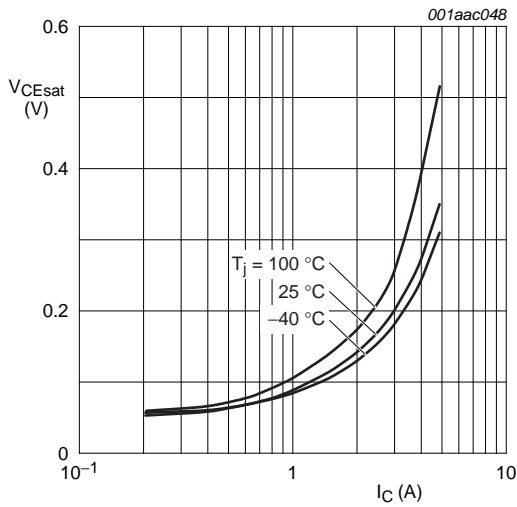
$T_j = 25\text{ °C}$.

Fig 11. Collector-emitter saturation voltage as a function of base current; typical values



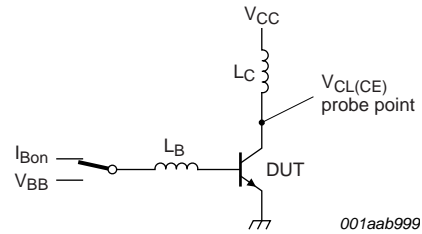
$I_C/I_B = 4$.

Fig 12. Base-emitter saturation voltage as a function of collector current; typical values



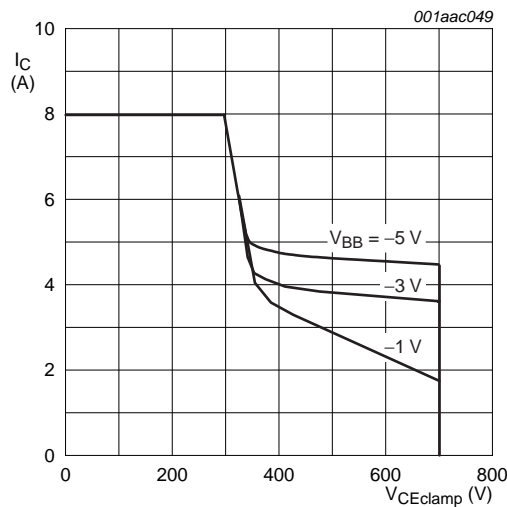
$I_C/I_B = 4$.

Fig 13. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CEclamp} < 700\text{ V}$; $V_{CC} = 150\text{ V}$; $V_{BB} = -5\text{ V}$, -3 V and -1 V ; $L_B = 1\ \mu\text{H}$; $L_C = 200\ \mu\text{H}$.

Fig 14. Test circuit for reverse bias safe operating area



$T_j < T_{j(max)}$.

Fig 15. Reverse bias safe operating area

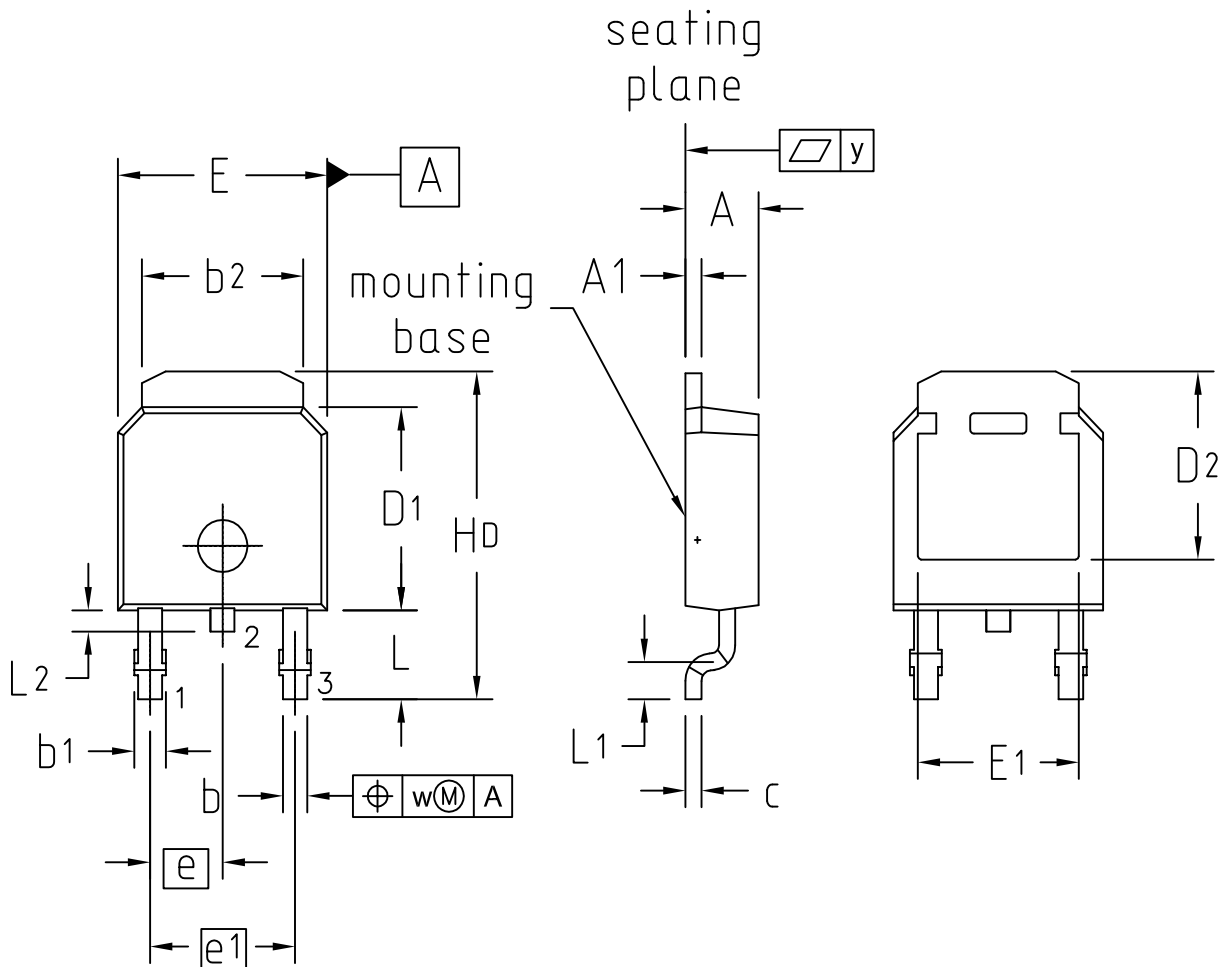
7. Package information

Epoxy meets requirements of UL94 V-0 at $1/8$ inch.

8. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428



UNIT	A	A ₁	b	b ₁	b ₂	c	D ₁	D ₂	E	E ₁	e	e ₁	H _D	L	L ₁	L ₂	w	y
mm	2.38	0.93	0.89	1.1	5.46	0.56	6.22	4.00	6.73	4.45	2.285	4.57	10.40	2.95	0.5	0.90	0.2	0.20
	2.22	0.46	0.71	0.9	5.00	0.20	5.98	min.	6.47	min.			9.60	2.55	min.	0.50	0.2	max.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT428		TO-252				

Fig. 2. Package outline DPAK (SOT428)

9. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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